

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

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Group Art Unit: 1742

Application No. 08/651,036

Filed: May 17, 1996

19/D

For:

METHOD EMPLOYING UV LASER PULSES OF VARIED

ENERGY DENSITY TO FORM DEPTHWISE SELF-LIMITING BLIND VIAS IN MULTILAYERED TARGETS 26 5/12/97

Date: May 1, 1998

Examiner: Gregory Mills

AMENDMENT

TO THE ASSISTANT COMMISSIONER FOR PATENTS:

In response to the April 3, 1998 Office action, please amend the above-identified patent application as follows.

In the Claims:

Amend claims 29 and 31 as follows:

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29. (Amended) The method of claim [28] 21 in which the second spatial spot size is greater than the first spatial spot size.

(Amended) A method for laser machining a blind via in a multilayered target including at least first and second conductor layers having respective first and second conductor ablation energy thresholds and a dielectric layer having surfaces and a dielectric ablation energy threshold, the first and second conductor layers positioned above and below, respectively, the surfaces of the dielectric layer, comprising:

generating, from a nonexcimer laser at a repetition rate of greater than about 200 Hz, a first laser output having a wavelength of less than 400 nm and containing at least one first laser pulse having a first energy density over a first spatial spot size and a temporal pulse width shorter than about

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